

| | Type | Hits | Search Text | DBs | Time Stamp |
|----|------|------|---|--|---------------------|
| 1 | BRS | 2 | jp-2000243856-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:40 |
| 2 | BRS | 2 | jp-2002246480-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:40 |
| 3 | BRS | 398 | first adj gate adj dielectric and second adj gate adj dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:41 |
| 4 | BRS | 263 | first adj gate adj dielectric with second adj gate adj dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:41 |
| 5 | BRS | 26 | first adj gate adj dielectric with second adj gate adj dielectric and gate adj dielectric with anneal\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:43 |
| 6 | BRS | 25 | first adj gate adj dielectric with second adj gate adj dielectric and gate adj dielectric with anneal\$3 and transistor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:43 |
| 7 | BRS | 65 | gate adj dielectric with anneal\$3 near2 rapid | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:45 |
| 8 | BRS | 4 | gate adj dielectric near2 anneal\$3 near2 rapid | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:44 |
| 9 | BRS | 16 | gate adj dielectric near5 anneal\$3 near2 rapid | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:44 |
| 10 | BRS | 2 | "5783469".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:45 |
| 11 | BRS | 0 | gate adj dielectric with thermal with oxidization with wet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:46 |

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| 12 | BRS | 10 | gate adj dielectric with thermal with oxidization | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 18:58 |
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|----|------|------|---|--|---------------------|
| 13 | BRS | 2 | "6525380".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:47 |
| 14 | BRS | 26 | gate adj dielectric with thermal with wet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/12 20:47 |
| 15 | BRS | 0 | gate adj dielectric with thermal with oxidization with wet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 18:59 |
| 16 | BRS | 74 | thermal with oxidization with wet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 18:59 |
| 17 | BRS | 20 | thermal with oxidization with wet with gate with (dielectric or insulat\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 18:59 |
| 18 | BRS | 29 | thermal with oxidization with wet with gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 19:04 |
| 19 | BRS | 39 | thermal near3 oxidization near3 wet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 19:08 |
| 20 | BRS | 14 | thermal near3 oxidization near3 wet and isolat\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 19:13 |
| 21 | BRS | 38 | thermal near3 oxidiz\$5 near3 wet and isolat\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 19:13 |
| 22 | BRS | 1017 | 438/151.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 20:30 |
| 23 | BRS | 69 | 438/219.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 20:31 |
| 24 | BRS | 857 | 438/275.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/13 20:31 |

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| 25 | BRS | 370 | 438/279.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB | 2004/11/13 20:31 |
| 26 | BRS | 963 | 438/287.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB | 2004/11/13 20:31 |
| 27 | BRS | 1092 | 438/585.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB | 2004/11/13 20:31 |
| 28 | BRS | 491 | 438/981.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB | 2004/11/13 20:31 |